

## : YUhiYg

Collector Power Dissipation:  $P_c=200\text{mW}$

Collector Current:  $I_c=-800\text{mA}$

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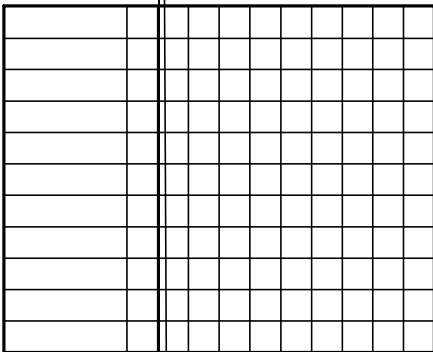
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CE0}$	-35	V
Collector-Base Voltage	$V_{CB0}$	-30	V
Emitter-Base Voltage	$V_{EB0}$	-5	V
Collector Current	$I_c$	-800	mA
Collector Power Dissipation	$P_c$	200	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 to 150	

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_c=-1\text{mA}, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_c=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=-1\text{mA}, I_c=0$	-5			V
Collector Cut-off Current	$I_{CB0}$	$V_{CB}=-30\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EB0}$	$V_{EB}=-5\text{V}, I_c=0$			-0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE}=-1\text{V}, I_c=-100\text{mA}$	100		320	
		$V_{CE}=-1\text{V}, I_c=-800\text{mA}$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=-500\text{mA}, I_B=-20\text{mA}$			-0.4	V
Transition Frequency	$f_T$	$V_{CE}=-5\text{V}, I_c=-10\text{mA}$		120		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		13		pF

Typical Characteristics

$I_C - V_{CE}$

COLLECTOR-EMITTER



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